

[METHOD FOR TREATING WAFER SURFACE]

Abstract

The present invention provides a method for treating the wafer surface, suitable for removing residues on the wafer surface. The method includes forming a photo-sensitive material layer over the wafer surface covering the bumps and the under bump metallurgy layer on the wafer surface. Using the bumps as masks, the photo-sensitive material layer is exposed and developed, to expose the wafer surface between the bumps. A wet etching process is then performed to remove residues on the exposed wafer surface and then the remained photo-sensitive material layer is removed.

Therefore, no residues remain on the wafer surface, and the yield of the bumps is increased.